PATENT COOPERATION TREATY

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INTERNATIONAL PRELIMINARY EXAMINATION REPORT

(PCT Article 36 and Rule 70)

Applicant's or agent's file reference						
30794.93WOU1	FOR FURTHER ACTION	See Notification of Transmittal of International Preliminary Examination Report (Form PCT/IPEA/416)				
International application No.	International filing date (day/mon	nth/year) Priority date (day/month/year)				
PCT/US03/21918	15 July 2003 (15.07.2003)	16 December 2002 (16.12.2002)				
International Patent Classification (IPC)	or national classification and IPC	1.00 - 00011001 - 2002 (10.121.2002)				
IPC(7): HO1L 21/00 and US Cl.: 438/46	5,481					
Applicant						
REGENTS OF THE UNIVERSITY OF	CALIFORNIA					
 This international preliminary examination report has been prepared by this International Preliminary Examining Authority and is transmitted to the applicant according to Article 36. This REPORT consists of a total of sheets, including this cover sheet. 						
2. This REPORT consists of	a total of sheets, including t	this cover sheet.				
which have been amer	nded and are the basis for this respectively (see Rule 70.16 and Section 60)	sheets of the description, claims and/or drawings report and/or sheets containing rectifications made 7 of the Administrative Instructions under the PCT).				
3. This report contains indicat	tions relating to the following it	teme.				
Friend.						
I Basis of the repo	ort .					
III Non-establishmer	nt of report with regard to nove	elty, inventive step and industrial applicability				
IV Lack of unity of	invention					
V Reasoned stateme	ent under Article 35(2) with reg	gard to novelty, inventive step or industrial				
VI Certain documen		ing such statement				
VII Certain defects in the international application						
VIII Certain observations on the international application						
Soluti objetvati	ons on the international applica	luon				
Date of submission of the demand	T Date of					
		f completion of this report				
06 May 2004 (06.05.2004)		2004 (10.06.2004)				
Name and mailing address of the IPEA/US		ized officer				
Mail Stop PCT, Attn: IPEA/US Commissioner for Patents						
P.O. Box 1450 Alexandria, Virginia 22313-1450	!	d Elms				
Facsimile No. (703)305-3230	Telepho	one No. 703.308.0956				
rm PCT/IPEA/409 (cover sheet)(July 1998)						

ANDREW Q.TRAN **PRIMARY EXAMINER**

INTERNATIONAL PRELIMINARY EXAMINATION REPORT

International application No.	
PCT/US03/21918	

ĺ	ĭ	Roci	s of the report
į			
	1.	With	regard to the elements of the international application:*
		M	the international application as originally filed.
		\bowtie	the description:
-			pages 1-19 as originally filed
			pages NONE , filed with the demand
			pages NONE, filed with the letter of
		\bowtie	the claims:
Į			pages 20-22 , as originally filed
1			pages NONE , as amended (together with any statement) under Article 19 pages NONE , filed with the demand
- 1			pages NONE, filed with the demand pages NONE, filed with the letter of
1		∇	·
- [the drawings: pages 1-6 as originally filed
- 1			pages 1-6, as originally filed pages NONE, filed with the demand
- 1			pages NONE, filed with the letter of
-			the sequence listing part of the description:
		ш,	pages NONE, as originally filed
			pages NONE , filed with the demand
l			pages NONE , filed with the letter of
	2.	With	regard to the language, all the elements marked above were excitable as 6 miles.
1			
1			verte available of furnished to this Authority in the following language which is:
		<u></u> _ ¹	the language of a translation furnished for the purposes of international search (under Rule23.1(b)).
		<u> </u>	the language of publication of the international application (under Rule 48.3(b)).
1		t	the language of the translation furnished for the purposes of international preliminary examination (under Rules
		:	55.2 and/or 55.3).
:	3 3	With	regard to any nucleotide and/or amino acid sequence disclosed in the international application, the
Ή.	i	nterna	ational preliminary examination was carried out on the basis of the sequence listing:
	ļ	ᆗᅧ	ontained in the international application in printed form.
	Ļ	_ f	iled together with the international application in computer readable form.
1.	[f	urnished subsequently to this Authority in written form.
1	L	fi	urnished subsequently to this Authority in computer readable form.
	Γ	T	The statement that the subsequently furnished written as well as
			The statement that the subsequently furnished written sequence listing does not go beyond the disclosure in the attendational application as filed has been furnished.
	L	_] T	he statement that the information recorded in computer readable form is identical to the written sequence listing as been furnished.
4	Г	_	
	. г	^ 	he amendments have resulted in the cancellation of:
İ		Ļ	the description, pages NONE
		Ļ	the claims, Nos. <u>NONE</u>
1	_	_, L	the drawings, sheets/fig NONE
5	٠L	_j m	his report has been established as if (some of) the amendments had not been made, since they have been considered to go
١.	_		
1	Ke _l	viucen	TEM STEELS WHICH have been furnished to the machine of the
*	An	y repl	as "originally filed" and are not annexed to this report since they do not contain amendments (Rules 70.16 and 70.17). acement sheet containing such amendments must be referred to under item 1 and annexed to this report.
			PEA/409 (Box I) (July 1998)
		~1/11	

INTERNATIONAL PRELIMINARY EXAMINATION REPORT

International application No. PCT/US03/21918

V. Reasoned statement under Rule 66.2(a)(ii) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement					
1. STATEMENT					
Novelty (N)	Claims Claims	1-19 NONE	_YES _NO		
Inventive Step (IS)	Claims Claims	1-19 NONE	_YES _NO		
Industrial Applicability (IA)	Claims Claims	NONE	_YES _NO		

2. CITATIONS AND EXPLANATIONS

Claims 1-19 meet the criteria set out in PCT Article 33(2)-(3), because the prior art does not teach or fairly suggest a method of performing a lateral epitaxial overgrowth of a planar, non-polar, a-plane gallium nitride (GaN) film, comprising (a) patterning a mask deposited on a substrate; and (b) performing a lateral epitaxial overgrowth of the GaN film off the substrate using hydride vapor phase epitaxy, wherein the GaN film nucleates only on portions of the substrate not covered by the patterned mask, the GaN film grows vertically through the openings in the patterned mask, and the GaN film then spreads laterally above the patterned mask and

Claims 1-19 meet the criteria set out in PCT Article 33(4), and thus has industrial applicability because the subject matter claimed can be made or used in the semiconductor industry.

Form PCT/IPEA/409 (Box V) (July 1998)